



TO-92 Plastic-Encapsulate Transistors

S8050 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 0.625 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

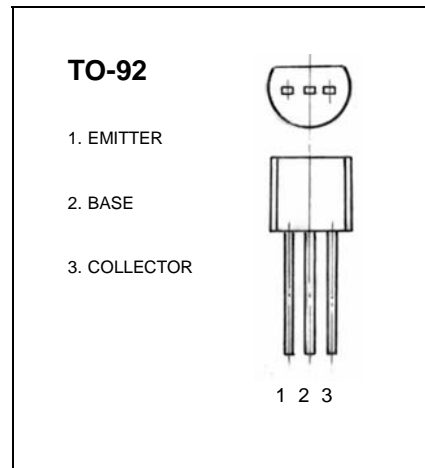
$$I_{CM}: 0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

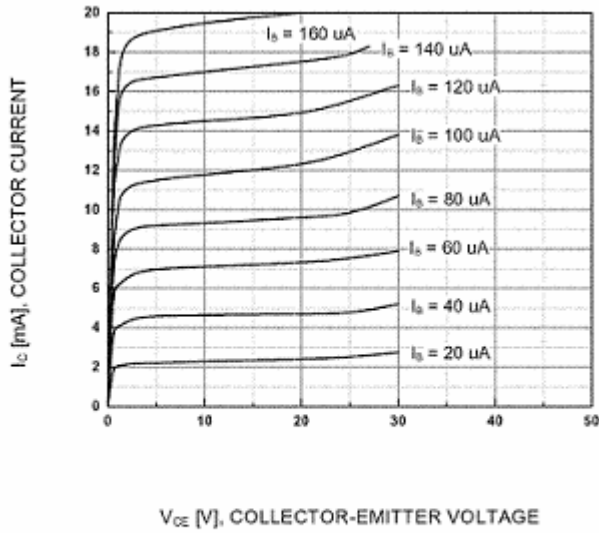
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 20\text{V}, I_B = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1\text{V}, I_C = 50\text{mA}$	85		300	
	$h_{FE(2)}$	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_C = 20\text{mA}$ $f = 30\text{MHz}$	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

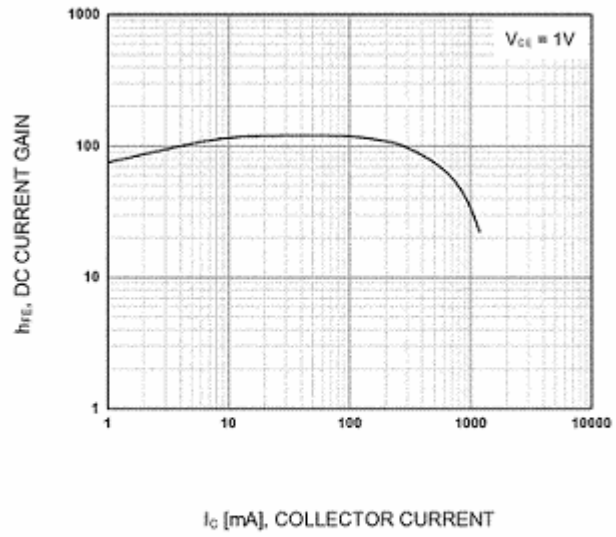
Rank	B	C	D
Range	85-160	120-200	160-300

Typical Characteristics

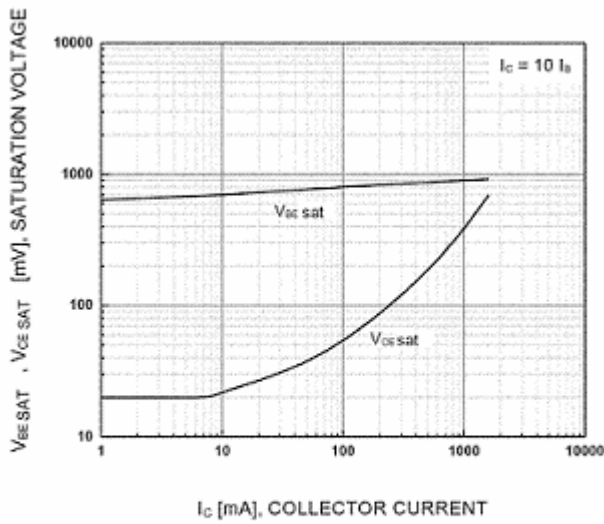
S8050



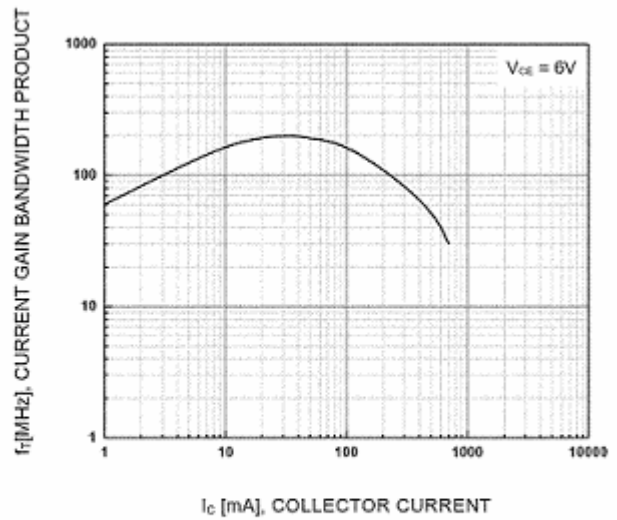
Static Characteristic



DC current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product